

Eric A Joseph

List of Publications by Year in descending order

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Version: 2024-02-01

43
papers

965
citations

516710

16
h-index

434195

31
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43
all docs

43
docs citations

43
times ranked

1115
citing authors

#	ARTICLE	IF	CITATIONS
1	Significance of plasma-photoresist interactions for atomic layer etching processes with extreme ultraviolet photoresist. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	4
2	Selective atomic layer etching of HfO ₂ over silicon by precursor and substrate-dependent selective deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	16
3	Preface for the Festschrift Honoring Dr. Steve Rosnagel. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	0
4	Nitride etching with hydrofluorocarbons III: Comparison of C ₄ H ₉ F and CH ₃ F for low- κ^2 nitride spacer etch processes. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, .	1.2	12
5	Nitride etching with hydrofluorocarbons. II. Evaluation of C ₄ H ₉ F for tight pitch Si ₃ N ₄ patterning applications. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, 031801.	1.2	10
6	Achieving ultrahigh etching selectivity of SiO ₂ over Si ₃ N ₄ and Si in atomic layer etching by exploiting chemistry of complex hydrofluorocarbon precursors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	40
7	Wafer-scale integration of sacrificial nanofluidic chips for detecting and manipulating single DNA molecules. Nature Communications, 2017, 8, 14243.	12.8	40
8	Characterizing fluorocarbon assisted atomic layer etching of Si using cyclic Ar/C ₄ F ₈ and Ar/CHF ₃ plasma. Journal of Chemical Physics, 2017, 146, 052801.	3.0	35
9	Highly selective dry etching of polystyrene-poly(methyl methacrylate) block copolymer by gas pulsing carbon monoxide-based plasmas. Journal Physics D: Applied Physics, 2017, 50, 204001.	2.8	8
10	Nitride etching with hydrofluorocarbons. I. Selective etching of nitride over silicon and oxide materials by gas discharge optimization and selective deposition of fluorocarbon polymer. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	17
11	Cyclic Cl ₂ /H ₂ quasi-atomic layer etching approach for TiN and TaN patterning using organic masks. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	7
12	Electron beam generated plasmas: Characteristics and etching of silicon nitride. Microelectronic Engineering, 2017, 168, 89-96.	2.4	24
13	Application of cyclic fluorocarbon/argon discharges to device patterning. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	17
14	Initial evaluation and comparison of plasma damage to atomic layer carbon materials using conventional and low $\langle i \rangle T_e \langle /i \rangle$ plasma sources. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	18
15	Fluorocarbon assisted atomic layer etching of SiO ₂ and Si using cyclic Ar/C ₄ F ₈ and Ar/CHF ₃ plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	74
16	High chi block copolymer DSA to improve pattern quality for FinFET device fabrication. Proceedings of SPIE, 2016, , .	0.8	16
17	Applications for Surface Engineering Using Atomic Layer Etching - Invited Paper. Solid State Phenomena, 2016, 255, 41-48.	0.3	1
18	Defect mitigation of plasma-induced delamination of TiW/Cu from SiN $\langle inf \rangle x \langle /inf \rangle$ layer in thin si interposer processing with glass carriers. , 2015, , .		0

#	ARTICLE	IF	CITATIONS
19	Self-aligned line-space pattern customization with directed self-assembly graphoepitaxy at 24nm pitch. Proceedings of SPIE, 2015, , .	0.8	2
20	Challenges of Tailoring Surface Chemistry and Plasma/Surface Interactions to Advance Atomic Layer Etching. ECS Journal of Solid State Science and Technology, 2015, 4, N5054-N5060.	1.8	45
21	Moving from thin films to atomic layers — Atomic layer etching. , 2015, , .		1
22	Electrical characterization of FinFETs with fins formed by directed self assembly at 29 nm fin pitch using a self-aligned fin customization scheme. , 2014, , .		0
23	CMOS-Compatible Self-Aligned In_{0.53}Ga_{0.47}As MOSFETs With Gate Lengths Down to 30 nm. IEEE Transactions on Electron Devices, 2014, 61, 3399-3404.	3.0	7
24	MIEC (mixed-ionic-electronic-conduction)-based access devices for non-volatile crossbar memory arrays. Semiconductor Science and Technology, 2014, 29, 104005.	2.0	45
25	Fluorocarbon assisted atomic layer etching of SiO ₂ using cyclic Ar/C ₄ F ₈ plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	2.1	161
26	Fabrication of sub-20 nm nanopore arrays in membranes with embedded metal electrodes at wafer scales. Nanoscale, 2014, 6, 8900-8906.	5.6	57
27	Two-Dimensional Pattern Formation Using Graphoepitaxy of PS- <i>b</i> -PMMA Block Copolymers for Advanced FinFET Device and Circuit Fabrication. ACS Nano, 2014, 8, 5227-5232.	14.6	143
28	Design and fabrication of a multiple-thickness electrochemical cantilever sensor. Microelectronic Engineering, 2014, 119, 1-5.	2.4	9
29	Pattern transfer of directed self-assembly (DSA) patterns for CMOS device applications. , 2013, , .		5
30	Subtractive W contact and local interconnect co-integration (CLIC). , 2013, , .		2
31	Pattern transfer of directed self-assembly patterns for CMOS device applications. Journal of Micro/Nanolithography, MEMS, and MOEMS, 2013, 12, 041305.	0.9	8
32	Integrated on-chip inductors with electroplated magnetic yokes (invited). Journal of Applied Physics, 2012, 111, .	2.5	43
33	The impact of melting during reset operation on the reliability of phase change memory. , 2012, , .		7
34	Fabrication of dual damascene BEOL structures using a multilevel multiple exposure (MLME) scheme, part 1: lithographic patterning. , 2010, , .		0
35	Fabrication of dual damascene BEOL structures using a multilevel multiple exposure (MLME) scheme, part 2: RIE-based pattern transfer and completion of dual damascene process yielding an electrically functional via chain. Proceedings of SPIE, 2010, , .	0.8	1
36	Influence of Bottom Contact Material on the Selective Chemical Vapor Deposition of Crystalline GeSbTe Alloys. Materials Research Society Symposia Proceedings, 2010, 1251, 10.	0.1	2

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37	Dynamic Resistance—A Metric for Variability Characterization of Phase-Change Memory. IEEE Electron Device Letters, 2009, 30, 126-129.	3.9	22
38	Generation of local magnetic fields at megahertz rates for the study of domain wall propagation in magnetic nanowires. Applied Physics Letters, 2009, 95, 262503.	3.3	2
39	The Influence of Nitrogen Doping on the Chemical and Local Bonding Environment of Amorphous and Crystalline Ge₂Sb₂Te₅. Materials Research Society Symposia Proceedings, 2009, 1160, 1.	0.1	3
40	Low-k spacers for advanced low power CMOS devices with reduced parasitic capacitances. , 2008, , .		3
41	Spectroscopic study of gas and surface phase chemistries of CF4 plasmas in an inductively coupled modified gaseous electronics conference reactor. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 114-125.	2.1	15
42	Effect of surface temperature on plasma-surface interactions in an inductively coupled modified gaseous electronics conference reactor. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1657-1667.	2.1	21
43	Modified gaseous electronics conference reference cell for the study of plasma-surface-gas interactions. Review of Scientific Instruments, 2004, 75, 884-890.	1.3	22